

TO-220 Plastic Package

CSB546

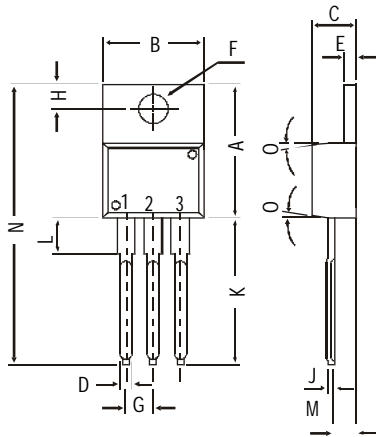
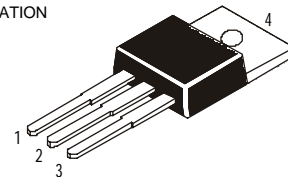
CSB546 PNP PLASTIC POWER TRANSISTOR

Complementary CSD401

TV Vertical Deflection Output

PIN CONFIGURATION

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



All dimensions in mm.

DIM	MIN.	MAX.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D		0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J		0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N		31.24
O		DEG 7

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)

 V_{CBO} max. 200 V

Collector-emitter voltage (open base)

 V_{CEO} max. 150 V

Collector current

 I_C max. 2 ATotal power dissipation up to $T_C = 25^\circ\text{C}$ P_{tot} max. 25 W

Junction temperature

 T_j max. 150 °C

Collector-emitter saturation voltage

 $I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$ V_{CEsat} max. 1.0 V

D.C. current gain

 $I_C = 0.4 \text{ A}; V_{CE} = 10 \text{ V}$ h_{FE} min. 40

max. 240

RATINGS (at $T_A=25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)

 V_{CBO} max. 200 V

Collector-emitter voltage (open base)

 V_{CEO} max. 150 V

Emitter-base voltage (open collector)

 V_{EBO} max. 5.0 V

Collector current

 I_C max. 2 A

CSB546

Total power dissipation up to $T_C = 25^\circ\text{C}$	P_{tot}	max.	25 W
Junction temperature	T_j	max.	150 °C
Storage temperature	T_{stg}	-65 to +150	°C

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

Collector cutoff current

$I_E = 0; V_{CB} = 150\text{ V}$

I_{CBO}	max.	50 μA
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Breakdown voltages

$I_C = 10\text{ mA}; I_B = 0$

V_{CEO}	min.	150 V
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$I_C = 500\ \mu\text{A}; I_E = 0$

V_{CBO}	min.	200 V
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$I_E = 500\ \mu\text{A}; I_C = 0$

V_{EBO}	min.	5.0 V
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Saturation voltages

$I_C = 500\text{ mA}; I_B = 50\text{ mA}$

V_{CEsat}	max.	1.0 V
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D.C. current gain

$I_C = 0.4\text{ A}; V_{CE} = 10\text{ V}^{**}$

h_{FE}	min.	40
	max.	240

Transition frequency

$I_C = 0.4\text{ A}; V_{CE} = 10\text{ V}$

f_T	typ.	5 MHz
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**** h_{FE} classification: R: 40-80 O: 70-140 Y: 120-240**

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/ CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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